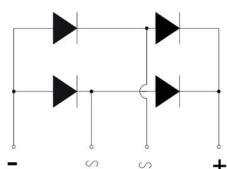
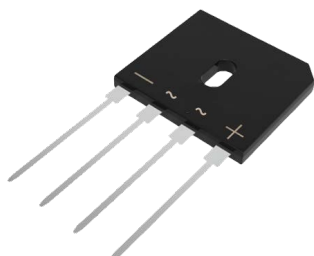


Low VF Bridge Rectifiers

GBU



Features

- Glass Passivated Chip Junction
- Low IRRM
- Ultra Low VF
- High VRRM

Benefits

- Case: GBU
- Terminals: Solderable Per MIL-STD-750
- Reduced power loss and switching transistor
- Reduced snubbing

Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	GBU1006L	Units
Maximum Repetitive Peak Reverse Voltage	VRRM	600	V
Maximum RMS voltage	VRMS	420	V
Maximum DC Blocking Voltage	VDC	600	V
Average Rectified Output Current	I _o	10	A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	IFSM	150	A
Maximum Forward Voltage at 5A	VF	0.92	V
Maximum DC Reverse Current @TA=25 °C at Rated DC Blocking Voltage @TA=125 °C	IR	10 500	μA
Typical Junction Capacitance (Note1)	Cj	25	pF
Operating and Storage Temperature Range	Tj, Tstg	-55 ~ +150	°C

Note: 1. Measured at 1MHz and applied reverse voltage of 4 VDC.

RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)

Fig.1 Current Derating, Case

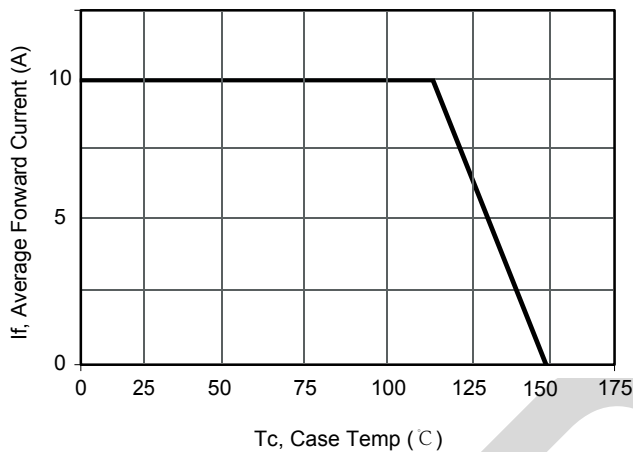


Fig.2 Maximum Non-Repetitive Peak Forward Surge Current

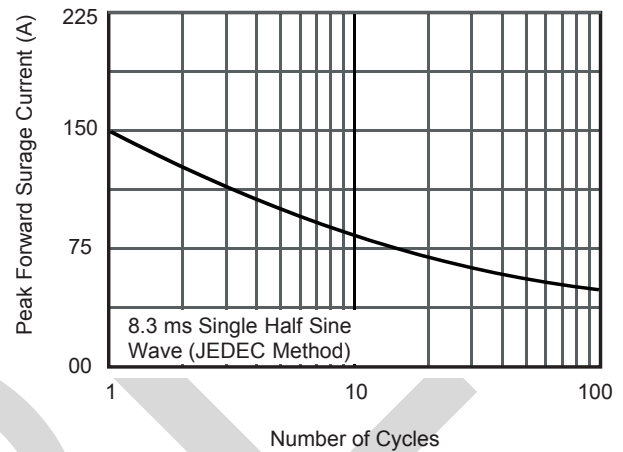


Fig.3 Typical Forward Voltage

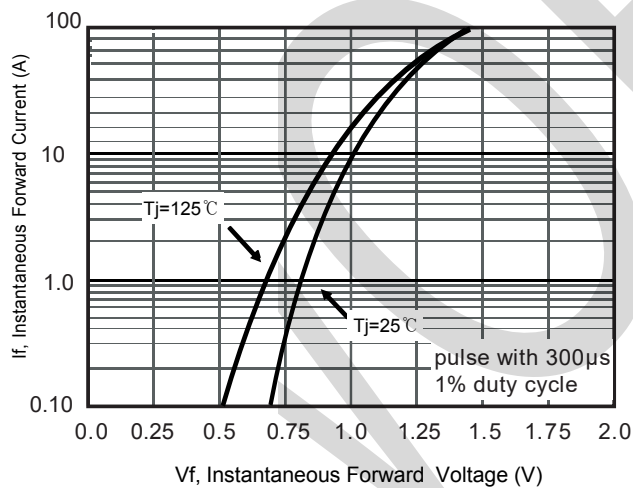
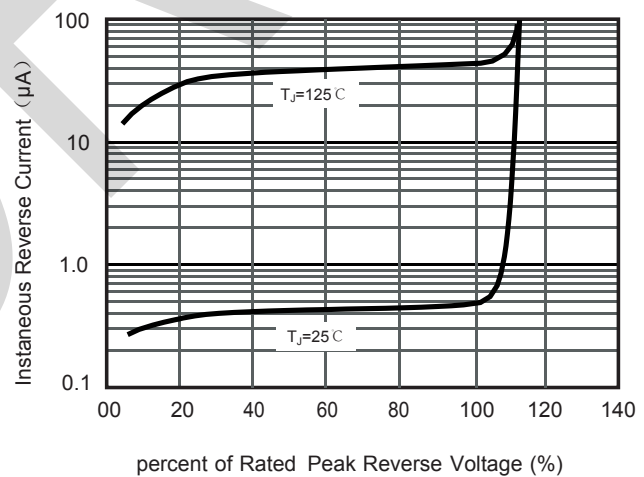
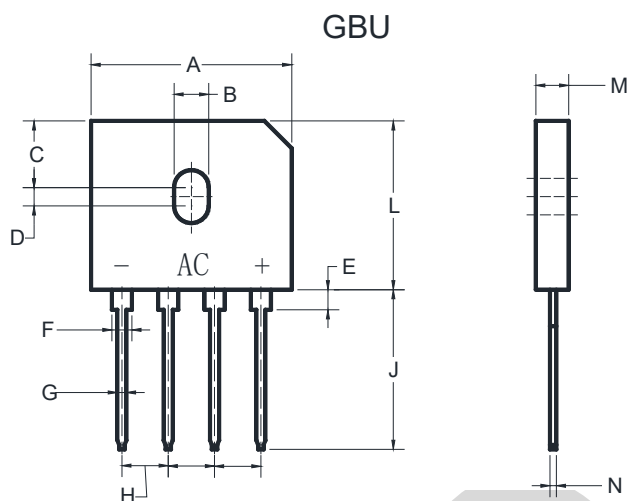


Fig.4 Typical Reverse Characteristics



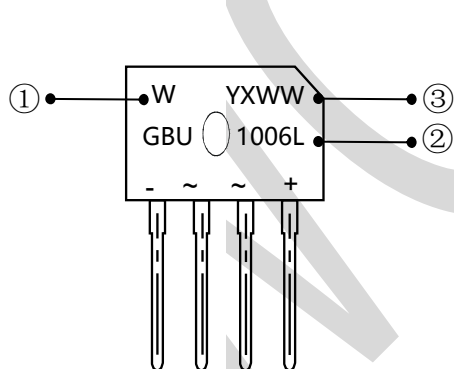
PACKAGE OUTLINE DIMENSIONS



Dimensions in millimeters

GBU		
Dim	Min	Max
A	21.70	22.50
B	3.40	4.10
C	7.40	8.00
D	1.65	2.26
E	2.25	2.85
F	2.05	2.4
G	1.02	1.37
H	4.83	5.43
J	17.0	18.6
L	18.3	18.9
M	3.30	3.66
N	0.46	0.66

Marking Information



- ① W : Company's trademark
- ② Product model : GBU1006L
- ③ PDC information :

Y X WW

WW:Week code(01 to 53)

X:Internal identification code

Y:Year code(ex:0=2020)